

N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

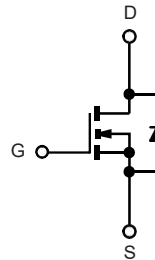
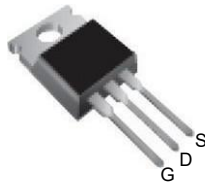
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a
60	0.011 at $V_{GS} = 10$ V	60
	0.013 at $V_{GS} = 4.5$ V	50

FEATURES

- 175 °C Junction Temperature
- TrenchFET[®] Power MOSFET
- Material categorization:


RoHS
 COMPLIANT

TO-220AB



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Gate-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current ($T_J = 175$ °C) ^b	I_D	$T_C = 25$ °C	60	
		$T_C = 100$ °C	50 ^a	
Pulsed Drain Current	I_{DM}	200	A	
Continuous Source Current (Diode Conduction)	I_S	50 ^a		
Avalanche Current	I_{AS}	50		
Single Avalanche Energy (Duty Cycle ≤ 1 %)	$L = 0.1$ mH	E_{AS}	125	mJ
Maximum Power Dissipation	P_D	$T_C = 25$ °C	136	W
		$T_A = 25$ °C	3 ^b , 8.3 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	15	18
		Steady State	40	50
Maximum Junction-to-Case	R_{thJC}	0.85	1.1	°C/W

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. $t \leq 10$ s.

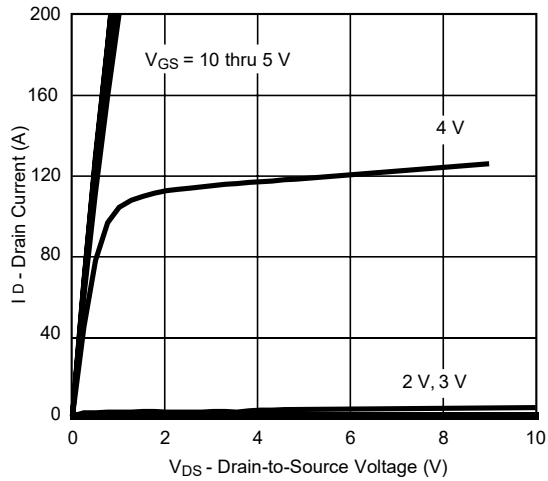
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	60			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.011		Ω
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.014		
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.018		
		$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$		0.013		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		60		S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4200		pF
Output Capacitance	C_{oss}			570		
Reverse Transfer Capacitance	C_{rss}			325		
Total Gate Charge ^c	Q_g	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		47		nC
Gate-Source Charge ^c	Q_{gs}			10		
Gate-Drain Charge ^c	Q_{gd}			12		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 50\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		10	20	ns
Rise Time ^c	t_r			15	25	
Turn-Off Delay Time ^c	$t_{d(off)}$			35	50	
Fall Time ^c	t_f			20	30	
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$)						
Pulsed Current	I_{SM}				60	A
Diode Forward Voltage	V_{SD}	$I_F = 20\text{ A}, V_{GS} = 0\text{ V}$		1	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		45	100	ns

Notes:

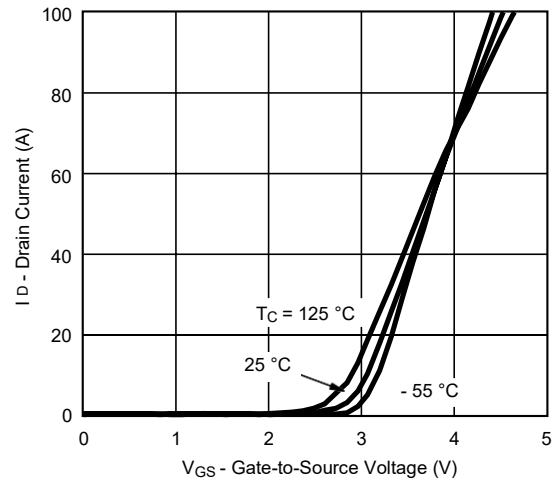
- a. For design aid only; not subject to production testing.
 b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

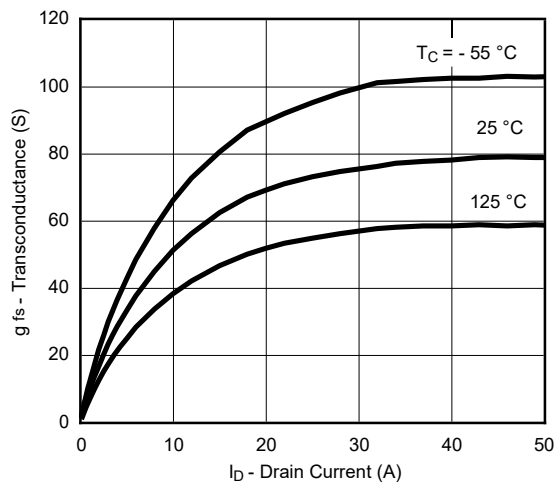
TYPICAL CHARACTERISTICS (25 °C unless noted)



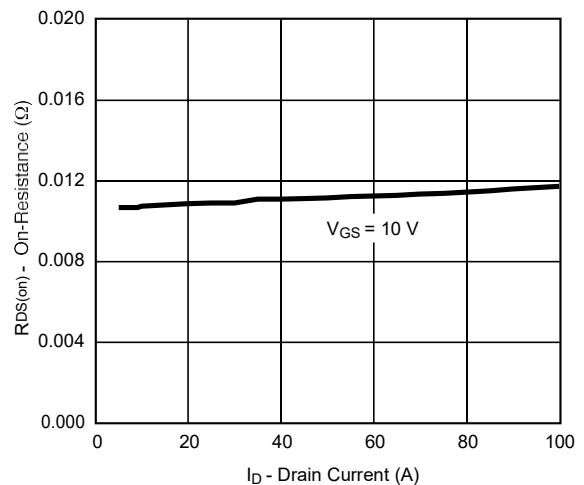
Output Characteristics



Transfer Characteristics



Transconductance



On-Resistance vs. Drain Current



Capacitance

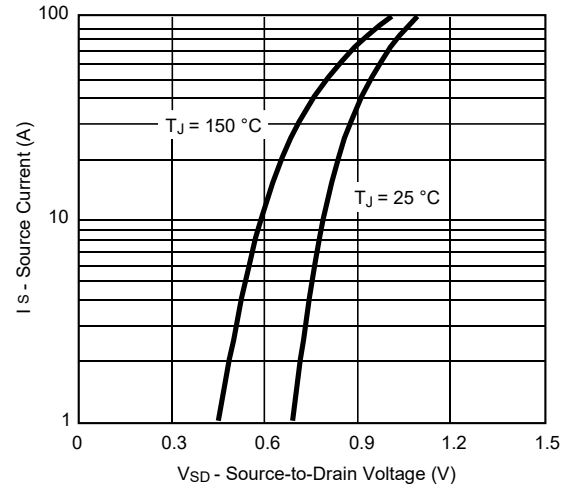


Gate Charge

TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature

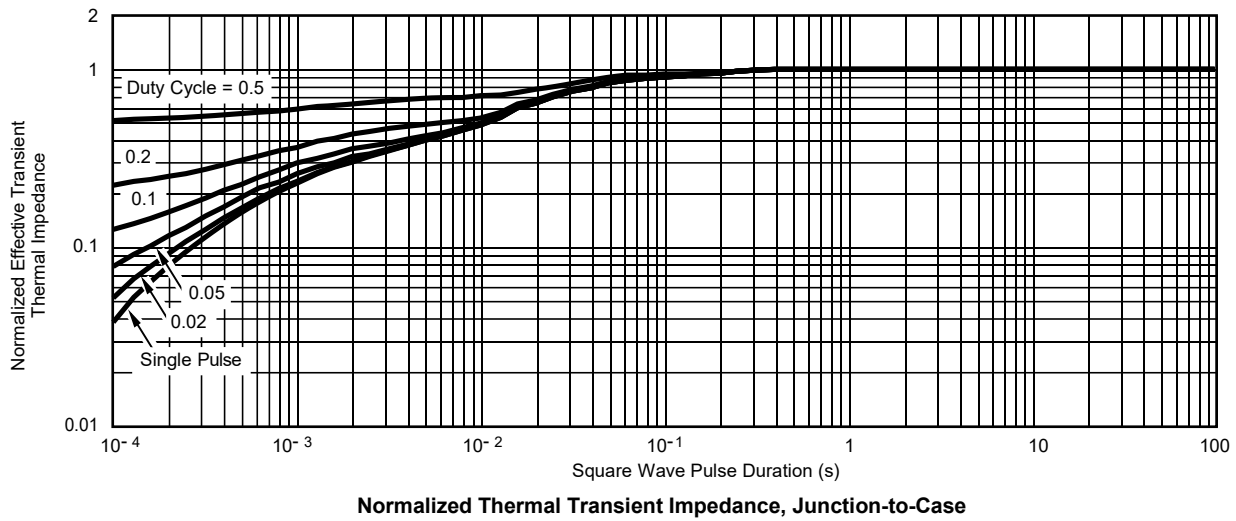
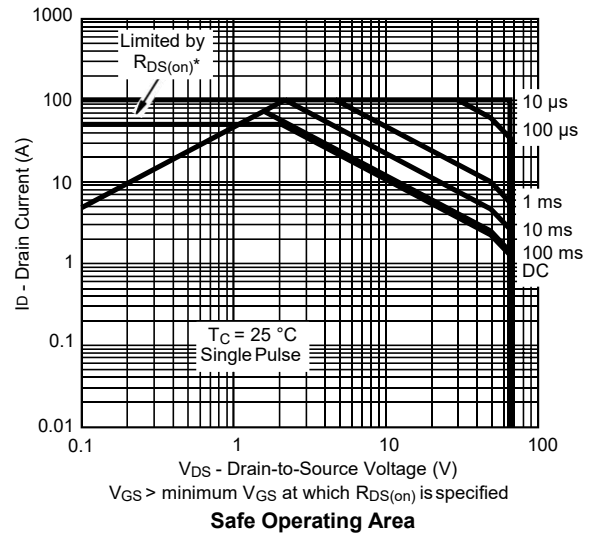


Source-Drain Diode Forward Voltage

THERMAL RATINGS



Maximum Drain Current vs. Ambient Temperature



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